

BUK7E2R7-30B

N-channel TrenchMOS standard level FET

Rev. 04 — 7 June 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V loads
- Automotive systems
- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

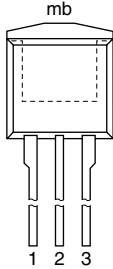
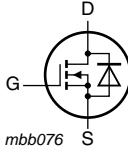
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	30	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C};$ see Figure 1 ; see Figure 3	[1]	-	75	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C};$ see Figure 2	-	-	300	W
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; T_j = 25\text{ °C};$ see Figure 11 ; see Figure 12	-	2.3	2.7	mΩ
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 75\text{ A}; V_{sup} \leq 30\text{ V};$ $R_{GS} = 50\text{ Ω}; V_{GS} = 10\text{ V};$ $T_{j(init)} = 25\text{ °C};$ unclamped	-	-	2.3	J
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10\text{ V}; I_D = 25\text{ A}; V_{DS} = 24\text{ V};$ $T_j = 25\text{ °C};$ see Figure 13	-	29	-	nC

[1] Continuous current is limited by package.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

SOT226 (I2PAK)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7E2R7-30B	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

4. Limiting values

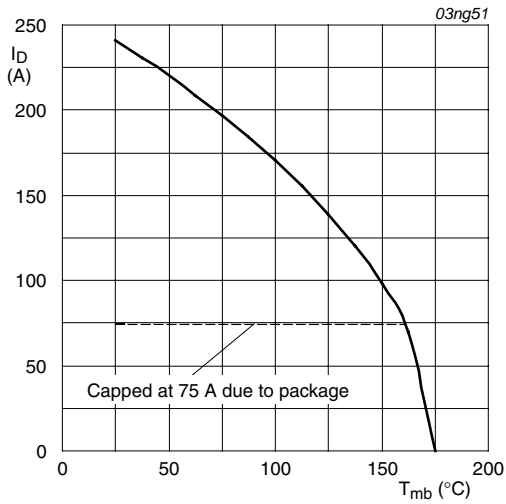
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	-	30	V	
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	-	30	V	
V_{GS}	gate-source voltage		-20	-	20	V	
I_D	drain current	$T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1 ; [1] see Figure 3	-	-	241	A	
		$T_{mb} = 100\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1 [2]	-	-	75	A	
		$T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; see Figure 1 ; [2] see Figure 3	-	-	75	A	
I_{DM}	peak drain current	$T_{mb} = 25\text{ °C}$; $t_p \leq 10\text{ }\mu\text{s}$; pulsed; see Figure 3	-	-	967	A	
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	-	300	W	
T_{stg}	storage temperature		-55	-	175	°C	
T_j	junction temperature		-55	-	175	°C	
Source-drain diode							
I_S	source current	$T_{mb} = 25\text{ °C}$	[1]	-	-	241	A
			[2]	-	-	75	A
I_{SM}	peak source current	$t_p \leq 10\text{ }\mu\text{s}$; pulsed; $T_{mb} = 25\text{ °C}$	-	-	967	A	
Avalanche ruggedness							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 75\text{ A}$; $V_{sup} \leq 30\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 10\text{ V}$; $T_{j(init)} = 25\text{ °C}$; unclamped	-	-	2.3	J	

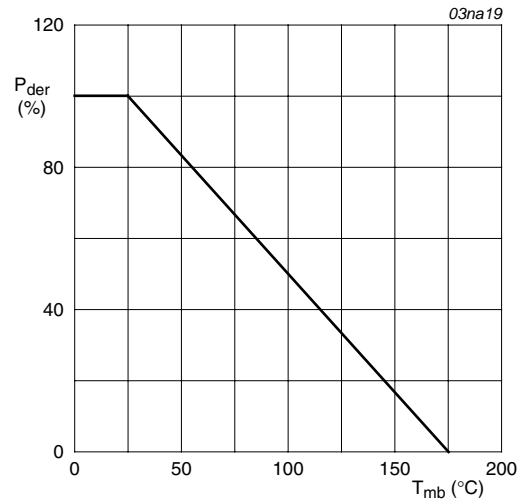
[1] Current is limited by power dissipation chip rating.

[2] Continuous current is limited by package.



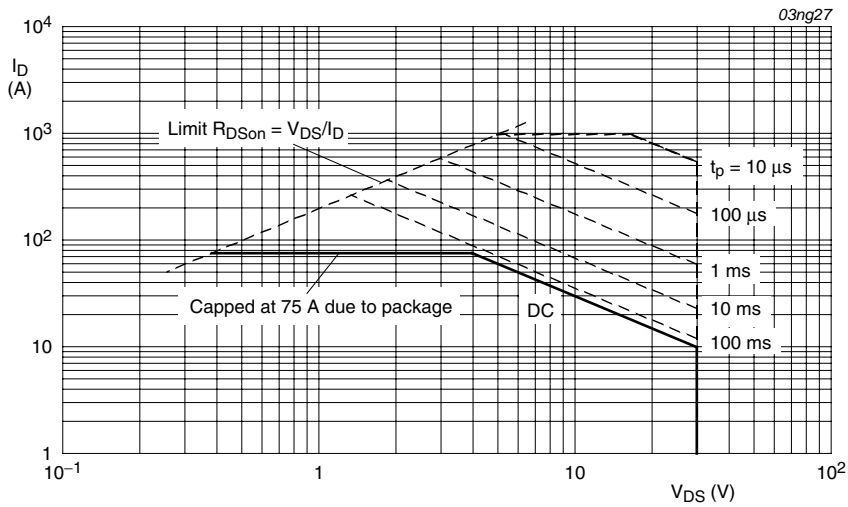
$$V_{GS} \geq 10V$$

Fig 1. Normalized continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$$T_{mb} = 25^{\circ}C; I_{DM} \text{ is single pulse}$$

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W

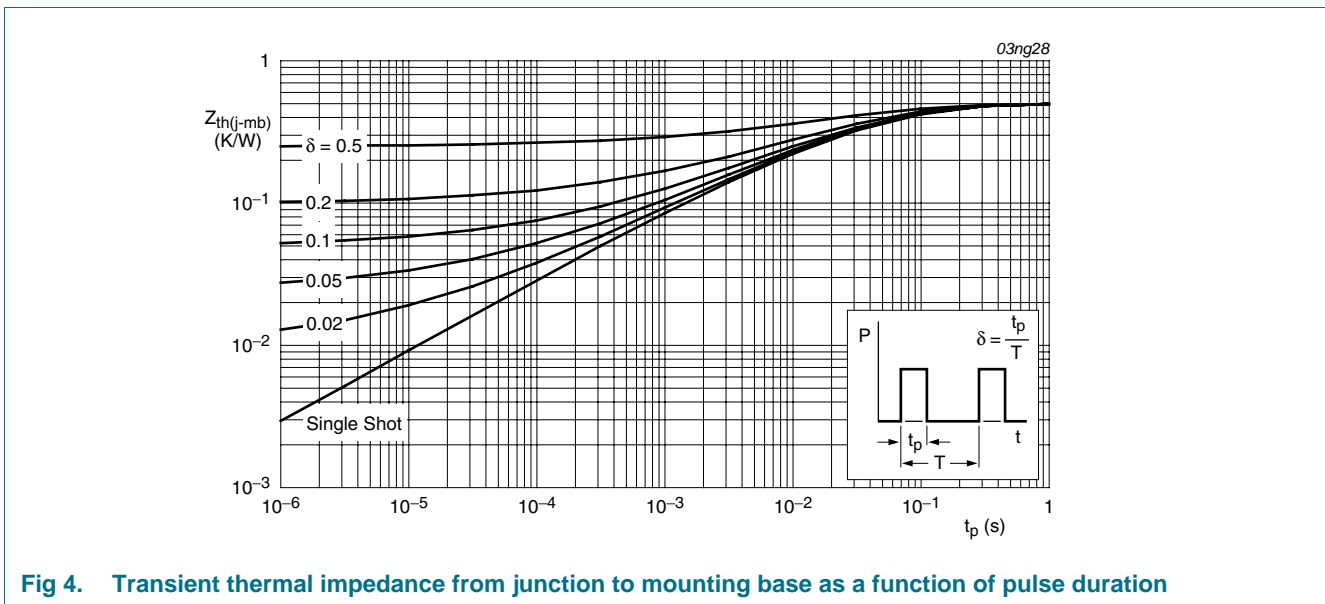
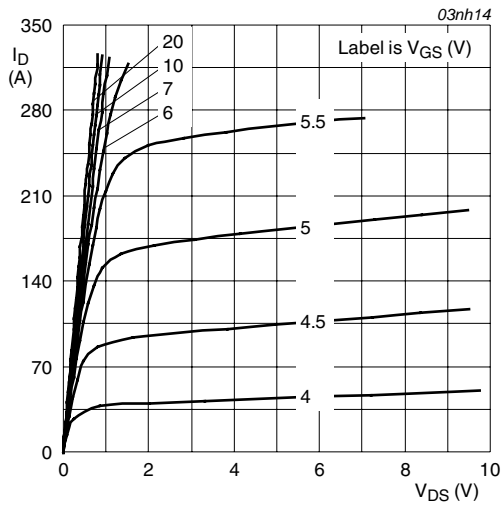


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

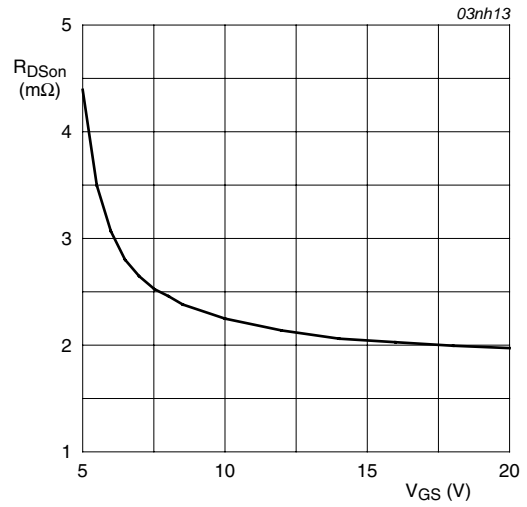
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	30	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 10	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 10	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see Figure 10	-	-	4.4	V
I_{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.02	1	μA
I_{GSS}	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 11 ; see Figure 12	-	-	5.1	m Ω
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 11 ; see Figure 12	-	2.3	2.7	m Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 13	-	91	-	nC
Q_{GS}	gate-source charge		-	19	-	nC
Q_{GD}	gate-drain charge		-	29	-	nC
C_{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 14	-	4659	6212	pF
C_{oss}	output capacitance		-	1691	2029	pF
C_{rss}	reverse transfer capacitance		-	622	852	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \text{ }^\circ\Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 10 \text{ }^\circ\Omega; T_j = 25 \text{ }^\circ\text{C}$	-	31	-	ns
t_r	rise time		-	107	-	ns
$t_{d(off)}$	turn-off delay time		-	113	-	ns
t_f	fall time		-	118	-	ns
L_D	internal drain inductance	from drain lead 6 mm from package to center of die ; $T_j = 25 \text{ }^\circ\text{C}$	-	4.5	-	nH
		from upper edge of drain mounting base to centre of die ; $T_j = 25 \text{ }^\circ\text{C}$	-	2.5	-	nH
L_S	internal source inductance	from source lead to source bond pad ; $T_j = 25 \text{ }^\circ\text{C}$	-	7.5	-	nH
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 40 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 15	-	0.85	1.2	V
t_{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s};$ $V_{GS} = -10 \text{ V}; V_{DS} = 20 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	88	-	ns
Q_r	recovered charge		-	132	-	nC



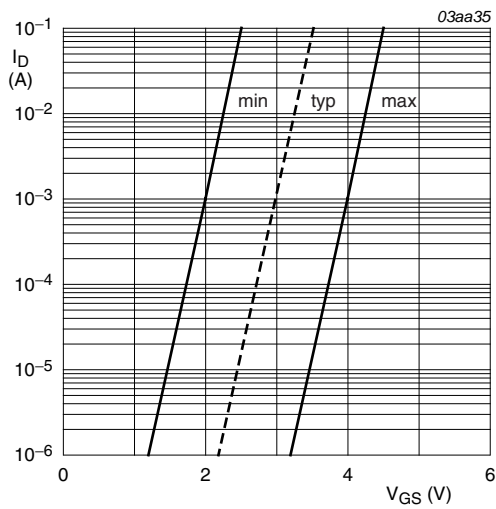
$T_j = 25^\circ\text{C}; t_p = 300\mu\text{s}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



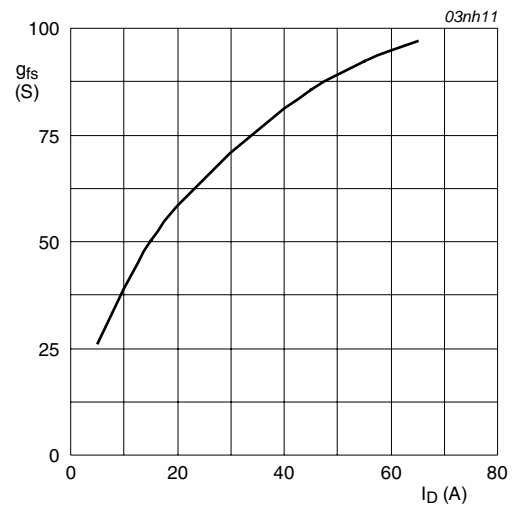
$T_j = 25^\circ\text{C}; I_D = 25\text{A}$

Fig 6. Drain-source on-state resistance as a function of drain current; typical values



$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$

Fig 7. Sub-threshold drain current as a function of gate-source voltage



$T_j = 25^\circ\text{C}; V_{DS} = 25\text{V}$

Fig 8. Forward transconductance as a function of drain current; typical values

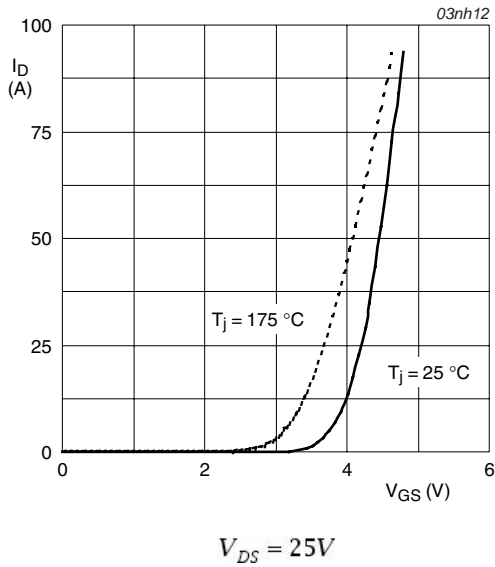


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

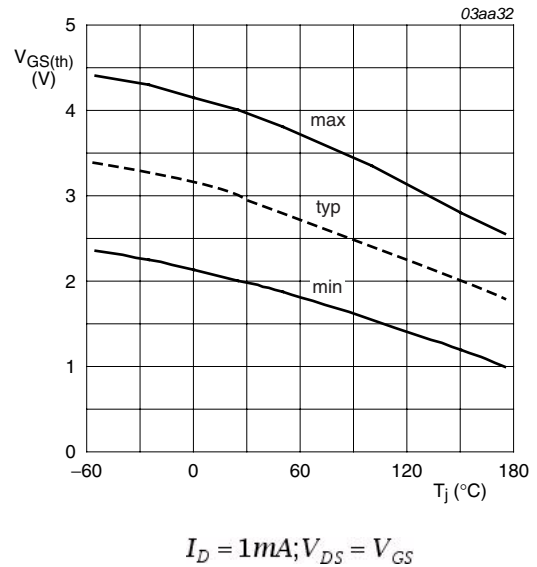


Fig 10. Gate-source threshold voltage as a function of junction temperature

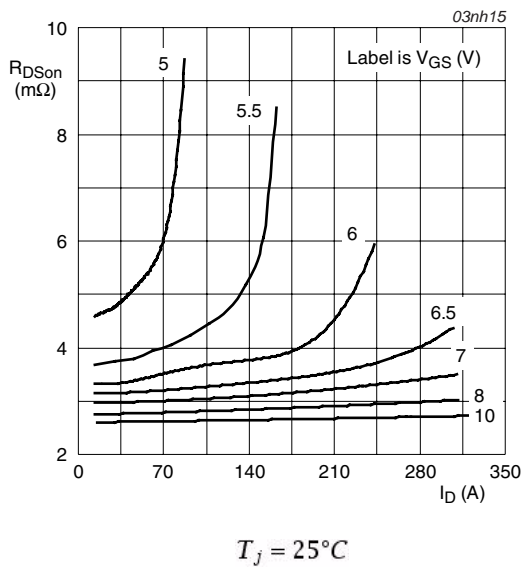


Fig 11. Drain-source on-state resistance as a function of drain current; typical values

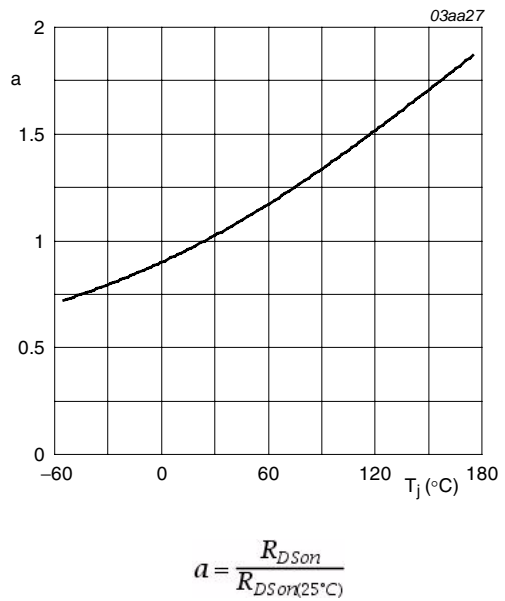
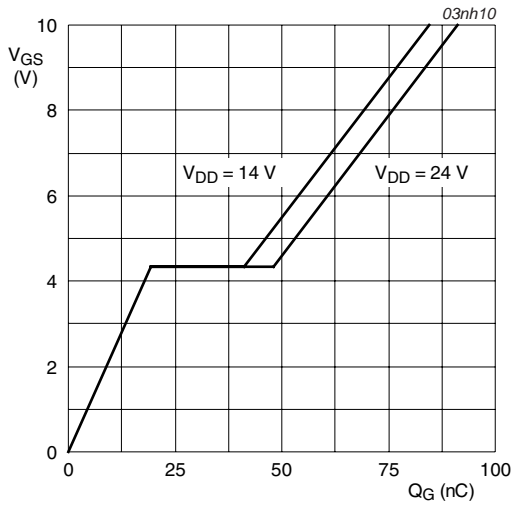
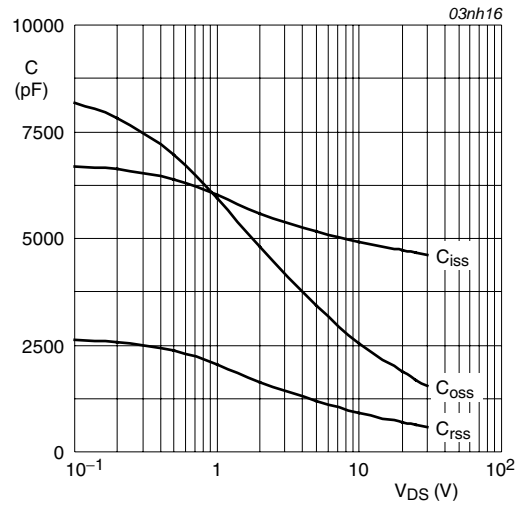


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



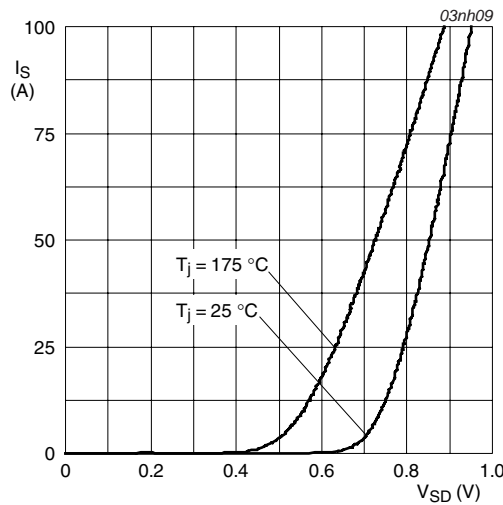
$T_j = 25^\circ\text{C}; I_D = 25\text{A}$

Fig 13. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\text{V}; f = 1\text{MHz}$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0\text{V}$

Fig 15. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended package (I2PAK); low-profile 3-lead TO-262

SOT226

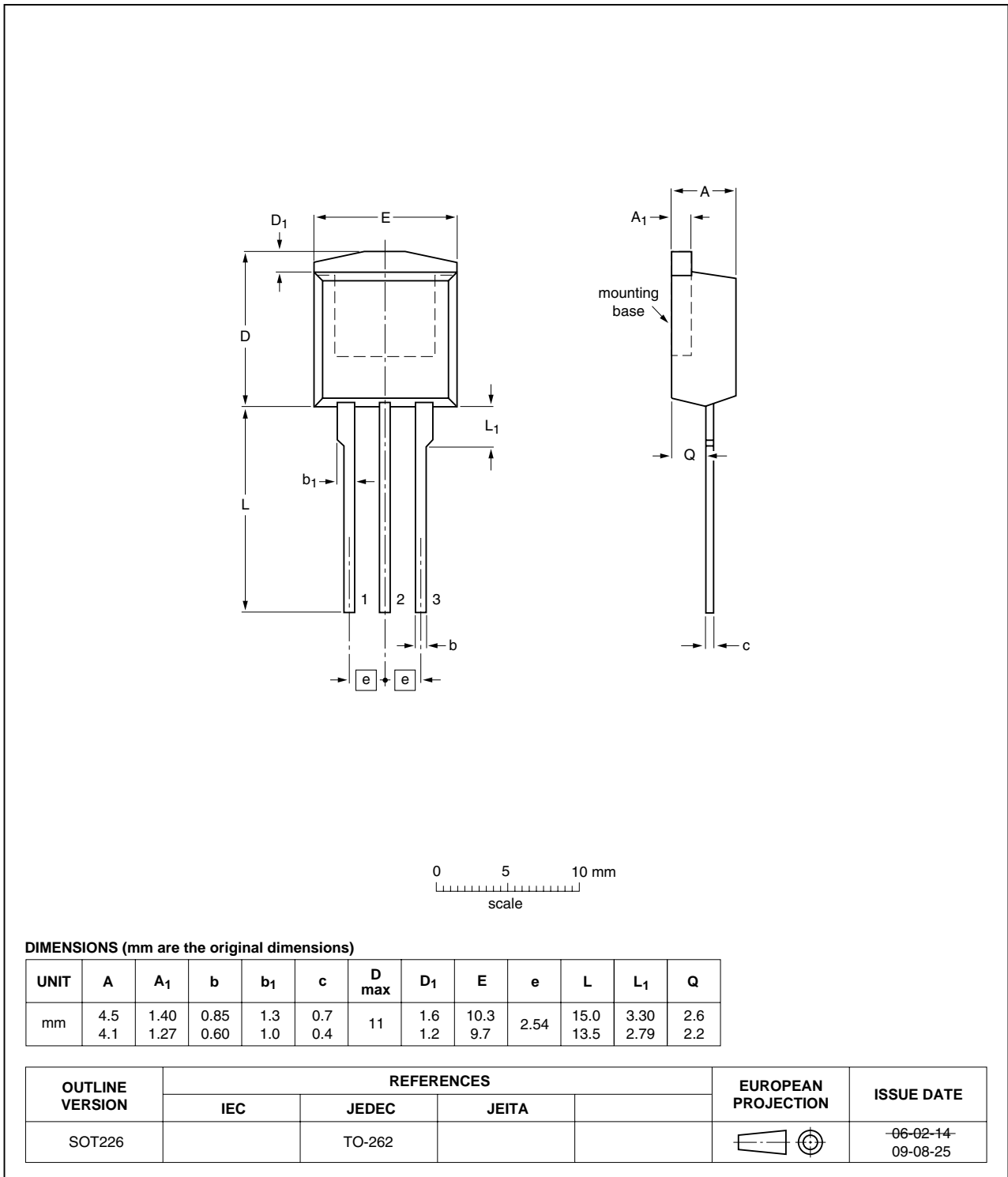


Fig 16. Package outline SOT226 (I2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7E2R7-30B v.4	20100607	Product data sheet	-	BUK75_76_7E2R7_30B_3
Modifications:		<ul style="list-style-type: none">• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.• Legal texts have been adapted to the new company name where appropriate.• Type number BUK7E2R7-30B separated from data sheet BUK75_76_7E2R7_30B_3.		
BUK75_76_7E2R7_30B_3 (9397 750 12048)	20031013	Product data	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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